- 8. Derive suitable expression and explain the vander paw and four point probe measurement for the carrier density of a semiconductor.
- 9. What are 3D, 2D, 1D and 0D systems/structures in solids ? Derive expression for the density of states and give plots between the density of state and energy for each system.

Roll No.

3003

B. Tech. 1st Semester (CSE) Examination – December, 2018

SEMICONDUCTOR PHYSICS

Paper: BSC-PHY-103-G

Time : Three Hours] [Maximum Marks : 75 Before answering the questions, candidates should ensure that they have been supplied the correct and complete question paper. No complaint in this regard, will be entertained after examination. Note: Attempt five questions in all, selecting one question from each Unit. Question No. 1 is compulsory. All questions carry equal marks. **1.** (a) Semiconductors have negative temperature coefficient of resistance. Explain its meaning. 2.5 (b) What are indirect and direct band gap semiconductors? 2.5(c) Discuss E-K diagrams and brief the origin of energy band in solids. 2.5 3003-1,650-(P-4)(Q-9)(18) P. T. O.

3003-1,650-(P-4)(Q-)(18) (4)

- (d) Calculate the static and dynamic resistance of a Ge diode at room temperature (25°C). Given reverse saturation current (I_s) = 1A, and bias voltage (V)=.5V. 2.5
- (e) Write a short note on (LDR) optoelectronic device.2.5
- (f) Give a brief explanation for hetrojunction devices.

2.5

UNIT-I

- 2. (a) Show that for a completely filled band in solids the number of effective electrons vanish.
 - (b) Discuss the motion of a free electron in one dimensional potential box and derive expressions for eigen wave function and eigen state.
- What is the effect of Periodic potential on the energy of an electron in a Metal ? Explain it on the basis of Kronig-Penny Model.

UNIT – II

- 4. (a) What do you understand by carrier transport phenomenon in semiconductors ? Discuss carrier transport through Diffusion.
- 3003-1,650-(P-4)(Q-2)(18) (2)

- (b) What are Ohmic and Schottky contacts with reference to metal-semiconductor junction. How they are different then a p-n junction?
- 5. (a) Show that Fermi level for an Intrinsic semiconductor lies exactly in the middle of valance band and conduction band.'
 - (b) What is an Intrinsic semiconductor ? Discuss the variation of Fermi level with temperature for an N-type semiconductor.

UNIT - III

- 6. (a) What is Density of states ? Derive an expression for joint density of states for a semiconductor substance.
 - (b) On account of optical transition, define induced absorption, spontaneous. emission and stimulated emission.
- 7. (a) What is transition rate ? Derive an expression for any one of the rate of transition (r_{sp}) for semiconductor substance. Also show how this transition rate (P_{sp}) varies with energy.
 10
 - (b) What is photovoltaic effect ? Give the construction and working of a Solar cell. 5

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